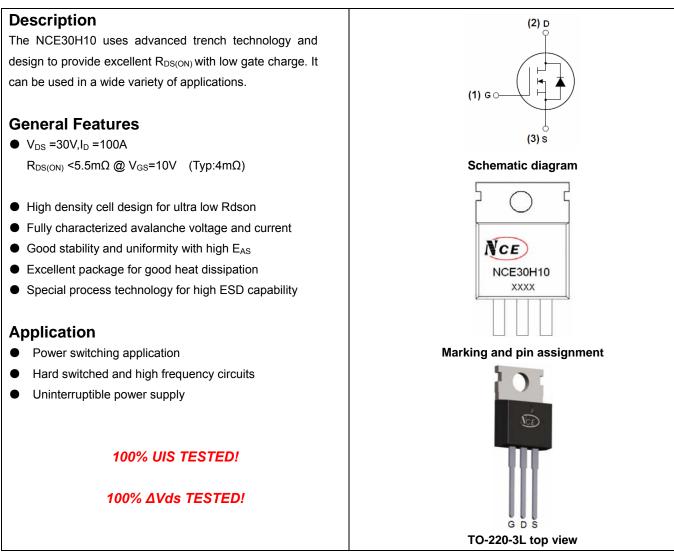


NCE N-Channel Enhancement Mode Power MOSFET



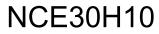
Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE30H10	NCE30H10	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	30	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	Ι _D	100	A
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	70	A
Pulsed Drain Current	I _{DM}	400	A
Maximum Power Dissipation	PD	110	W
Single pulse avalanche energy (Note 5)	E _{AS}	350	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C





Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	1.36	°C/W
--	------------------	------	------

Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·	·	•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	·	·	•			
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1	1.6	3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	4.0	5.5	mΩ
Forward Transconductance	g fs	V _{DS} =10V,I _D =20A	50	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}			3300		PF
Output Capacitance	C _{oss}			356		PF
Reverse Transfer Capacitance	C _{rss}			308		PF
Switching Characteristics (Note 4)	·	·	•			
Turn-on Delay Time	t _{d(on)}		-	11	-	nS
Turn-on Rise Time	tr	$V_{DS}=25V, V_{GS}=0V,$ F=1.0MHz $V_{DD}=15V, I_{D}=30A$ $V_{GS}=4.5V, R_{GEN}=1.8\Omega$	-	160	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =4.5V, R_{GEN} =1.8 Ω	-	25	-	nS
Turn-Off Fall Time	t _f		-	60	-	nS
Total Gate Charge	Qg			70		nC
Gate-Source Charge	Q _{gs}	V _{DS} =15V,I _D =30A, V _{GS} =10V		8.8		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V		16.3		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =30A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S	-	-	-	100	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 30A	-	56	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	110	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negl	igible (turi	n-on is do	minated b	y LS+LD)

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t \leq 10 sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

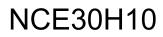
4. Guaranteed by design, not subject to production

5. EAS condition: Tj=25 $^\circ \!\! \mathbb{C}$,V_{DD}=15V,V_G=10V,L=0.5mH,Rg=25\Omega



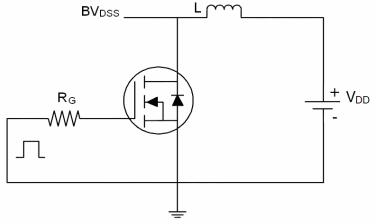
http://www.ncepower.com

Pb Free Product

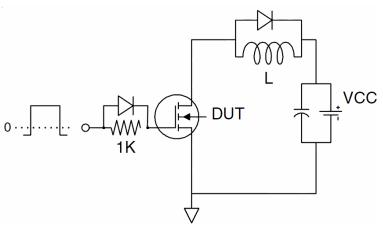


Test circuit

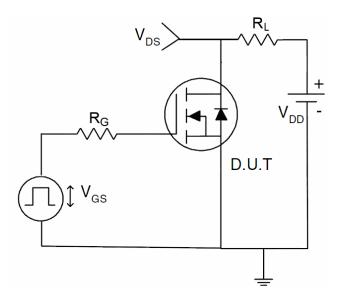
1) E_{AS} test Circuits



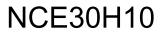
2) Gate charge test Circuit:



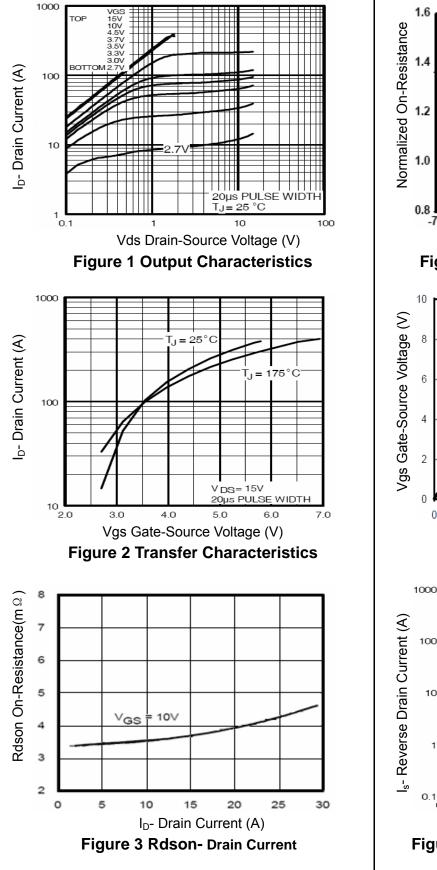
3) Switch Time Test Circuit:

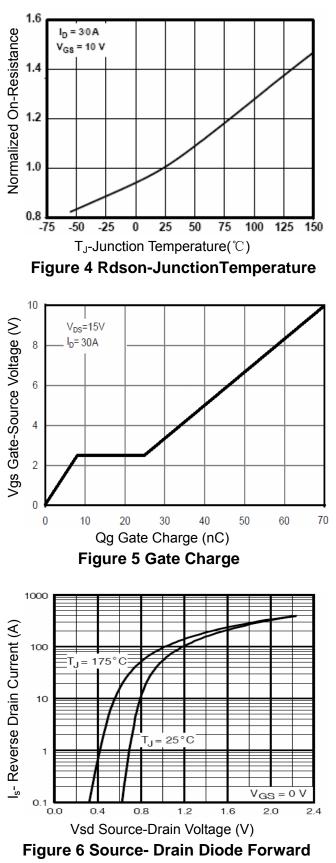






Typical Electrical and Thermal Characteristics (Curves)







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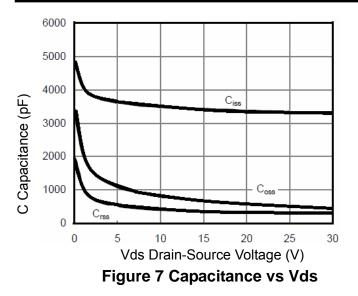
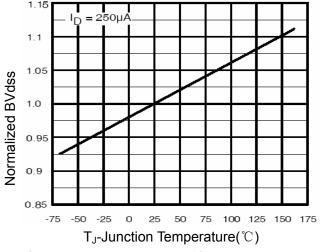


Figure 8 Safe Operation Area



Pb Free Product

NCE30H10

Figure 9 BV_{DSS} vs Junction Temperature

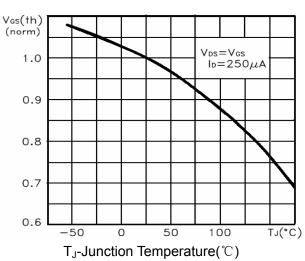
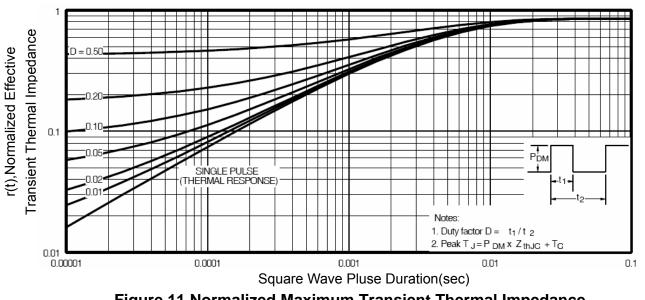
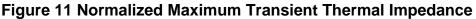


Figure 10 V_{GS(th)} vs Junction Temperature





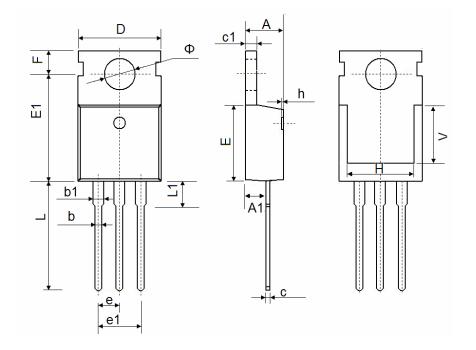


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NCE30H10

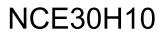
TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295	REF.	
Φ	3.400	3.800	0.134	0.150	







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